

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SD798

DESCRIPTION

- With TO-220 package
- High voltage
- DARLINGTON

APPLICATIONS

- With switching and igniter applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

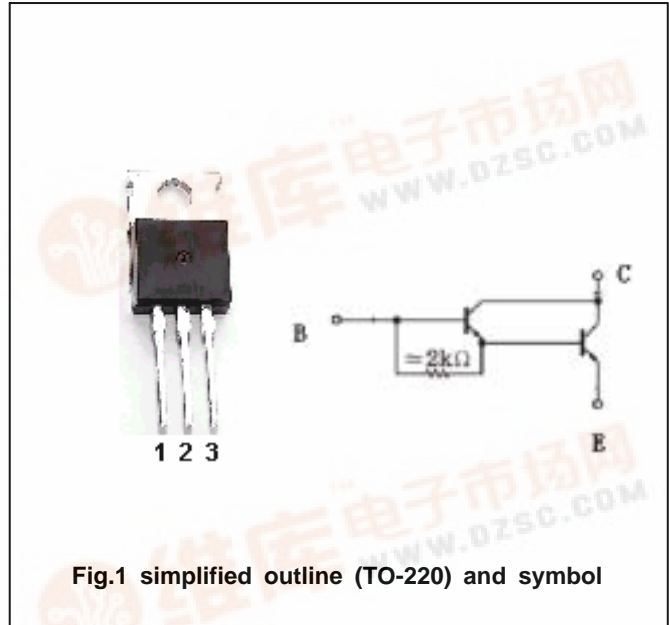


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _{CBO}	Collector-base voltage	Open emitter	600	V
V _{CEO}	Collector-emitter voltage	Open base	300	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		6	A
I _B	Base current		1	A
P _C	Collector power dissipation	T _C =25	30	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.5A ; L=40mH	300			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A ; I _B =0.04A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A ; I _B =0.04A			2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =600V; I _E =0			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.5	mA
h _{FE-1}	DC current gain	I _C =2A ; V _{CE} =2V	1500			
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =2V	200			
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =50V		35		pF

Switching times

t _{on}	Turn-on time	I _{B1} =-I _{B2} =0.04A V _{CC} 100V, R _L =25		1		μs
t _{stg}	Storage time			8		μs
t _f	Fall time			5		μs

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PACKAGE OUTLINE

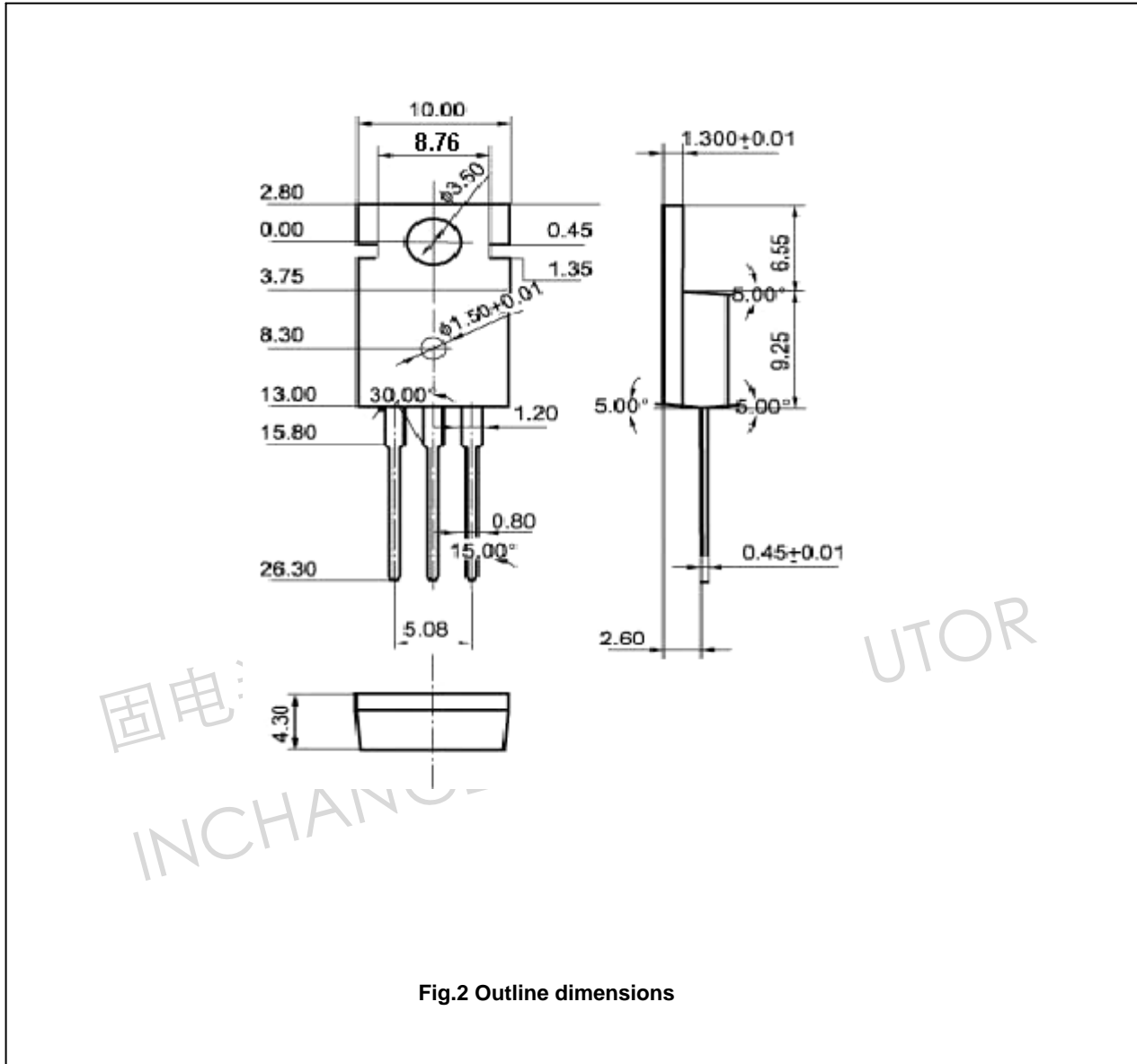


Fig.2 Outline dimensions